## **EUROPEAN PATENT OFFICE**

**(A)** 

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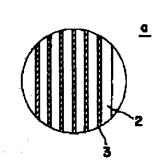
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TITLE : SEMICONDUCTOR DEVICE AND ITS

MANUFACTURING METHOD

(B)

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ABSTRACT: PROBLEM TO BE SOLVED: To manufacture a compact and high-performance semiconductor device by easily fabricating the semiconductor device in an arbitrary shape.

> SOLUTION: A semiconductor device consists of a flexible film-shaped insulation substrate 2 such as polyimide and Teflon and a semiconductor 3 for thermoelectric conversion being formed on the entire surface of its single surface and the semiconductor 3 is fabricated by rolling the film-shaped insulation substrate 2. The semiconductor 3 is either a P-type thermoconversion semiconductor or N-type thermoconversion semiconductor in ultra-lattice structure by an ultra-thin film.

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